USN

Sixth Semester B.E. Degree Examination, June/July 2017

Lithography Techniques

Max. Marks: 100 Time: 3 hrs.

> Note: Answer FIVE full questions, selecting at least TWO questions from each part.

PART - A

1	a.	What is the principle of Lithography? Explain about optical lithography with neat diagram.	
		(08 Marks)	

(07 Marks) Explain about multistage scanner resolution with examples. h

Which are the factors affecting construction and maintenance of a clean room. (05 Marks)

Explain about phase shift mask and the principle involved in it. (07 Marks) 2 a.

Describe about binary mask with diagram. (06 Marks) b.

Explain in detail about attenuated phase shift mask with a neat diagram. (07 Marks)

(10 Marks) Explain about extreme ultraviolet lithography. 3 a.

Describe zone plate array lithography with diagram. State its advantages over other types of b. (10 Marks) lithography.

(10 Marks) Explain in detail about scanning electron beam lithography. 4 a.

Explain about parallel direct - write e-beam systems electron beam projection lithography.

(10 Marks)

PART - B

	a.	Discuss about electron scattering and proximity correction.	(06Marks)
		Explain about electron beam nano-lithography with diagram.	(10 Marks)
	0	Define and explain about shot noise and substrate charging	(04 Marks)

Define and explain about shot noise and substrate charging.

Describe about focused ion beam lithography. (10 Marks) 6 a.

Explain in detail about ion beam lithography. (07 Marks) b. (03 Marks)

State applications of masked ion lithography. c.

What is soft lithography? Explain nano imprint lithography with various steps involved. 7 a.

(08 Marks)

Explain about NIL-Hot Embossing with diagram. State its advantages. (12 Marks) b.

Explain about types of etching with neat diagram. State their advantages and limitations. 8 a.

(12 Marks)

Explain about reactive ion etching. b.

(04 Marks)

Discuss about wet etching of silicon.

(04 Marks)

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